



40V N-CHANNEL ENHANCEMENT MODE MOSFET

Product Summary

BV _{DSS}	R _{DS(ON)}	I _D T _A = +25°C		
40V	0.05Ω @ $V_{GS} = 10V$	7A		

Description

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

Applications

- DC-DC Converters
- Audio Output Stages
- · Relay and Solenoid Driving
- Motor Control

Features

- Low On-Resistance
- Fast Switching Speed
- Low Threshold
- Low Gate Drive
- Lead-Free Finish; RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability
- An Automotive-Compliant Part is Available Under Separate Datasheet (ZXMN4A06GQ)

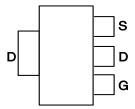
Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic, UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe;
 Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.112 grams (Approximate)

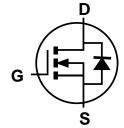




Top View



Pin Out - Top View



Equivalent Circuit

Ordering Information (Note 4)

Part Number	Compliance	Case	Packaging
ZXMN4A06GTA	Standard	SOT223	1,000/Tape & Reel
ZXMN4A06GTC	Standard	SOT223	4,000/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information

ZXMN * 4A06 *

SOT223

ZXMN4A06 = Product Type Marking Code YWW = Date Code Marking Y or \overline{Y} = Last Digit of Year (ex: 6 = 2016) WW or $\overline{W}W$ = Week Code (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	40	V
Gate-Source Voltage			V_{GS}	±20	V
		(Note 6)		7	
Continuous Drain Current	$V_{GS} = 10V$	$T_A = +70^{\circ}C \text{ (Note 6)}$	I _D	5.6	А
		(Note 5)		5	
Pulsed Drain Current	V _{GS} = 10V	(Note 7)	I _{DM}	22	Α
Continuous Source Current (Body Diode) (Note 6)		Is	5.4	Α	
Pulsed Source Current (Body Diode) (Note 7)		I _{SM}	22	А	

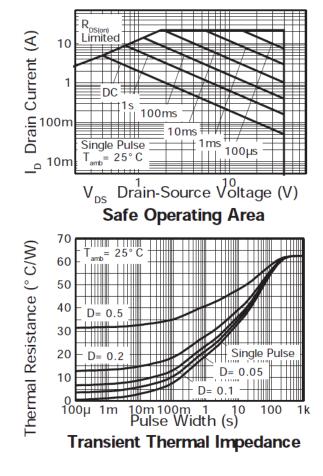
Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

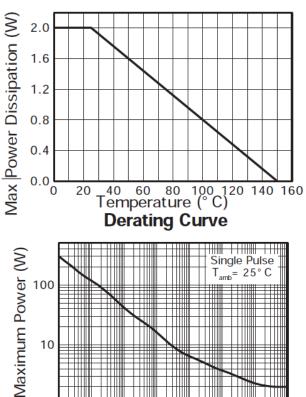
Characteristic	Symbol	Value	Unit		
Power Dissipation	(Note 5)		2 16	W	
Linear Derating Factor	(Note 6)	P _D	3.9 31	mW/°C	
Thermal Resistance, Junction to Ambient	(Note 7)	D	62.5	°C/W	
Thermal Resistance, Junction to Ambient	(Note 6)	R _{0JA}	32.2		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C		

Notes:

- 5. For a device surface mounted on 25mm x 25mm FR-4 PCB with high coverage of single sided 1oz copper, in still air conditions.
- 6. For a device surface mounted on FR-4 PCB measured at t \leq 5 seconds.
- 7. Repetitive rating 25mm x 25mm FR-4 PCB, D = 0.05, pulse width 10µs pulse width limited by maximum junction temperature.

Thermal Characteristics





Pulse Power Dissipation

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Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

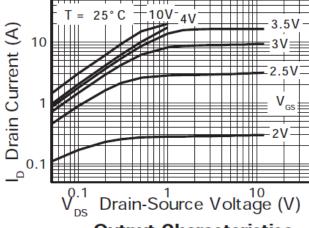
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV _{DSS}	40	_		V	$I_D = 250\mu A, V_{GS} = 0V$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μΑ	V _{DS} = 40V, V _{GS} = 0V	
Gate-Source Leakage	I _{GSS}	_	_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS							
Gate Threshold Voltage	V _{GS(TH)}	1	_	2	V	$I_D=250\mu A,V_{DS}=V_{GS}$	
Static Drain Source On Registence (Note 9)	0	_		0.05	Ω	V _{GS} = 10V, I _D = 4.5A	
Static Drain-Source On-Resistance (Note 8)	R _{DS(ON)}		_	0.075		$V_{GS} = 4.5V, I_D = 3.2A$	
Forward Transconductance	g fs	_	8.7	_	S	$V_{DS} = 15V, I_D = 2.5A$	
Diode Forward Voltage (Note 8)	V_{SD}	_	0.8	0.95	V	$I_S = 2.5A$, $V_{GS} = 0V$, $T_J = +25$ °C	
Reverse Recovery Time (Note 9)	t _{RR}	_	19.86	_	ns	$I_F = 2.5A$, di/dt = 100A/ μ s, $T_J = +25^{\circ}$ C	
Reverse Recovery Charge (Note 9)	Q_{RR}	_	16.36	_	nC		
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C _{iss}	_	770	_	pF		
Output Capacitance	Coss	_	92	_	pF	$V_{DS} = 40V, V_{GS} = 0V$ of = 1MHz	
Reverse Transfer Capacitance	C _{rss}	_	61	_	pF	1 = 11VII 12	
Total Gate Charge	Qg	_	18.2	_	nC	.,	
Gate-Source Charge	Q _{gs}	_	2.1	_	nC	$V_{DS} = 30V$, $V_{GS} = 10V$, $I_{D} = 2.5A$ (Refer to test circuit)	
Gate-Drain Charge	Q_{gd}	_	4.5	_	nC		
Turn-On Delay Time	t _{D(ON)}	_	2.55	_	ns	V _{DD} = 30V, V _{GS} = 10V	
Turn-On Rise Time	t _r	_	4.45	_	ns		
Turn-Off Delay Time	t _{D(OFF)}	_	28.61	_	ns	$I_D = 2.5A, R_G \cong 6\Omega$ (Refer to test circuit)	
Turn-Off Fall Time	t _f	_	7.35		ns	(Note: to test official)	

Notes:

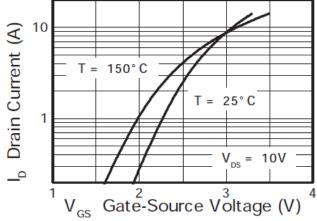
^{8.} Short duration pulse test used to minimize self-heating effect. 9. Guaranteed by design. Not subject to product testing.



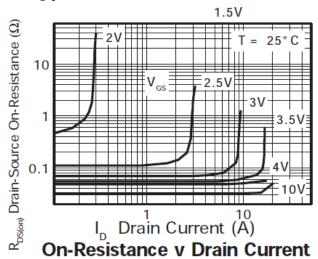
Typical Characteristics

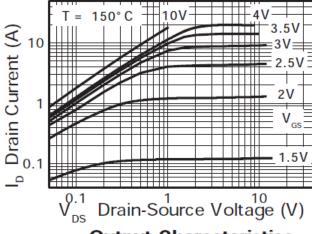


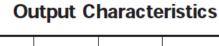
Output Characteristics

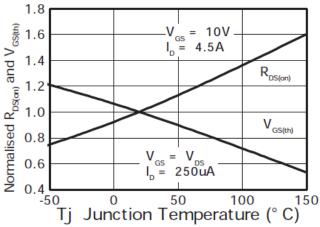


Typical Transfer Characteristics

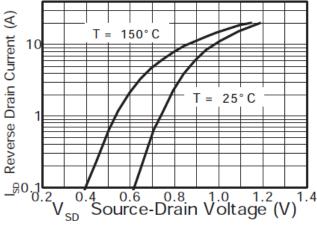








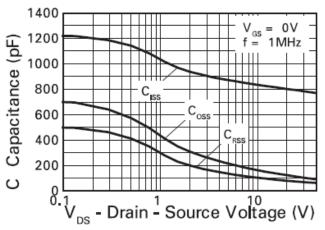
Normalised Curves v Temperature



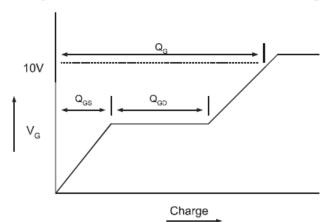
Source-Drain Diode Forward Voltage



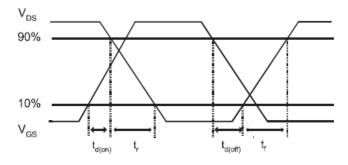
Typical Characteristics (Cont.)



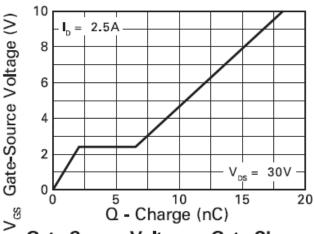
Capacitance v Drain-Source Voltage



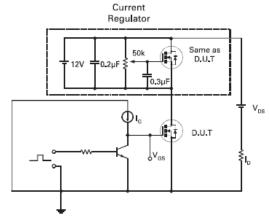
Basic Gate Charge Waveform



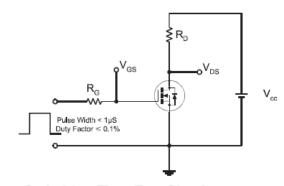
Switching Time Waveforms



Gate-Source Voltage v Gate Charge



Gate Charge Test Circuit

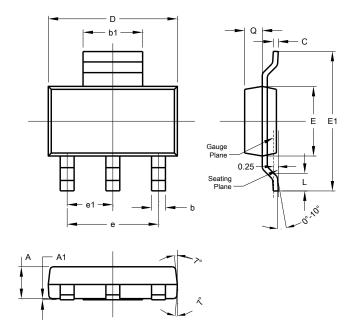


Switching Time Test Circuit



Package Outline Dimensions

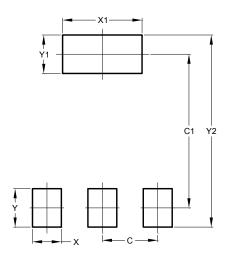
Please see http://www.diodes.com/package-outlines.html for the latest version.



SOT223					
Dim	Min	Max	Тур		
Α	1.55	1.65	1.60		
A1	0.010	0.15	0.05		
b	0.60	0.80	0.70		
b1	2.90	3.10	3.00		
С	0.20	0.30	0.25		
D	6.45	6.55	6.50		
E	3.45	3.55	3.50		
E1	6.90	7.10	7.00		
е	-	-	4.60		
e1	-	-	2.30		
L	0.85	1.05	0.95		
Q	0.84	0.94	0.89		
All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.



Dimensions	Value (in mm)		
С	2.30		
C1	6.40		
X	1.20		
X1	3.30		
Υ	1.60		
Y1	1.60		
V2	8 00		



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